

isc Silicon NPN Power Transistor
2SC4573
DESCRIPTION

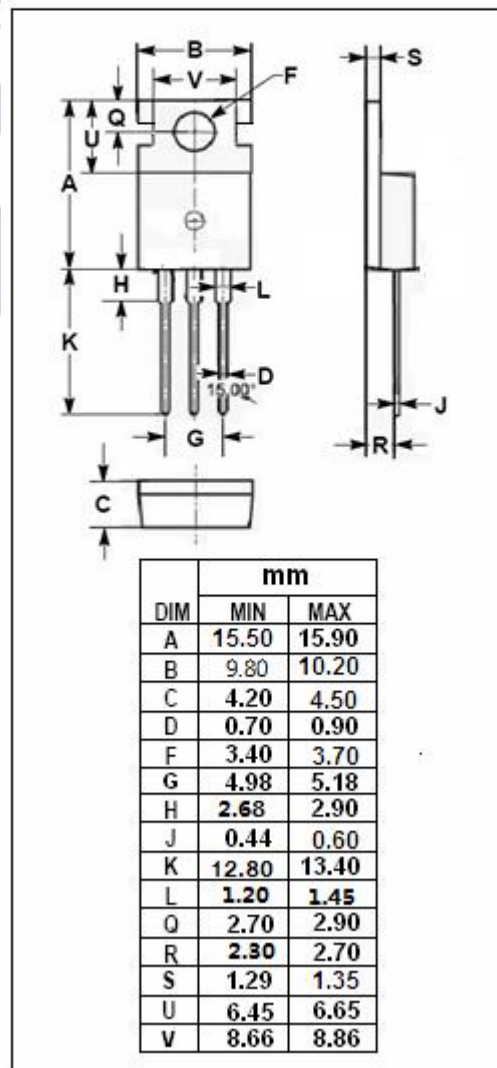
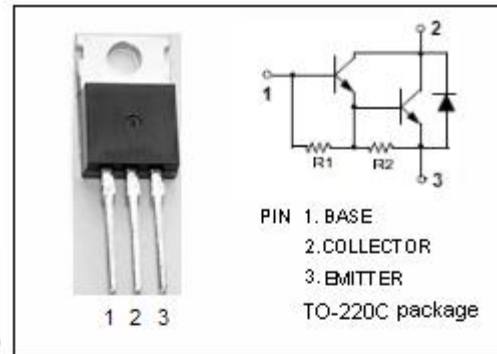
- Low Collector Saturation Voltage
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 60V$ (Min)
- Good Linearity of h_{FE}
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in humidifier , DC/DC converter and general purpose applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Collector Current-Pulse	6	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ C$	35	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon NPN Power Transistor**2SC4573****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; I _B = 0	60			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.5A; I _B = 5mA			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.5A; I _B = 5mA			2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			5	mA
h _{FE}	DC Current Gain	I _C = 1.5A ; V _{CE} = 3V	2000		10000	